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PATENT APPLICATION

THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of

Docket No: Q66212

HIROYUKI, KIYOKU, et al.

Appln. No.: 09/986,332

Group Art Unit: 1765

Confirmation No.: 5542

Examiner: Anderson, Matthew A.

Filed: November 08, 2001

For: NITRIDE SEMICONDUCTOR GROWTH METHOD, NITRIDE SEMICONDUCTOR SUBSTRATE, AND NITRIDE SEMICONDUCTOR DEVICE

**RESPONSE TO RESTRICTION REQUIREMENT and
AMENDMENT UNDER 37 C.F.R. § 1.111**

Commissioner for Patents
Washington, D.C. 20231

Sir:

In response to the Office Action dated May 2, 2002, please amend the above-identified application as follows:

IN THE CLAIMS:

Please enter the following amended claims:

49. (Amended) A method according to claim 48, wherein:

a total area of upper surfaces of portions, of the underlayer, which are covered with said first selective growth mask is larger than that of portions, of the underlayer, which are exposed from the first windows;

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a total area of upper surfaces of portions, of the first nitride semiconductor portions, which are covered with said second selective growth mask is larger than that of portions, of the first nitride semiconductor portions, which are exposed from the second windows;

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